

Silicon NPN Power Transistors

2SD2333

DESCRIPTION

- With TO-3PML package
- High breakdown voltage
- Built-in damper diode

APPLICATIONS

Color TV horizontal deflection output applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

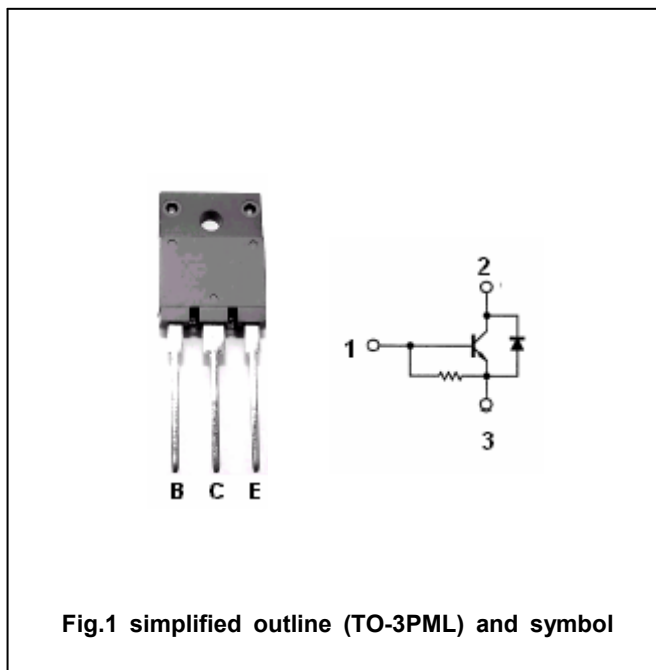


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|------------------|---------|------|
| V_{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V_{CEO} | Collector-emitter voltage | Open base | 600 | V |
| V_{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I_C | Collector current | | 5 | A |
| I_{BM} | Base current-peak | | 2.5 | A |
| P_C | Collector power dissipation | $T_C=25^\circ C$ | 80 | W |
| T_j | Junction temperature | | 150 | °C |
| T_{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =100mA; I _B =0 | 800 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =200mA, I _C =0 | 5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =4A; I _B =0.8A | | | 5.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =4A; I _B =0.8A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =500V; I _E =0 | | | 10 | μA |
| h _{FE} | DC current gain | I _C =1A; V _{CE} =5V | 8 | | | |
| V _F | Diode forward voltage | I _F =5A | | | 2.0 | V |

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PACKAGE OUTLINE

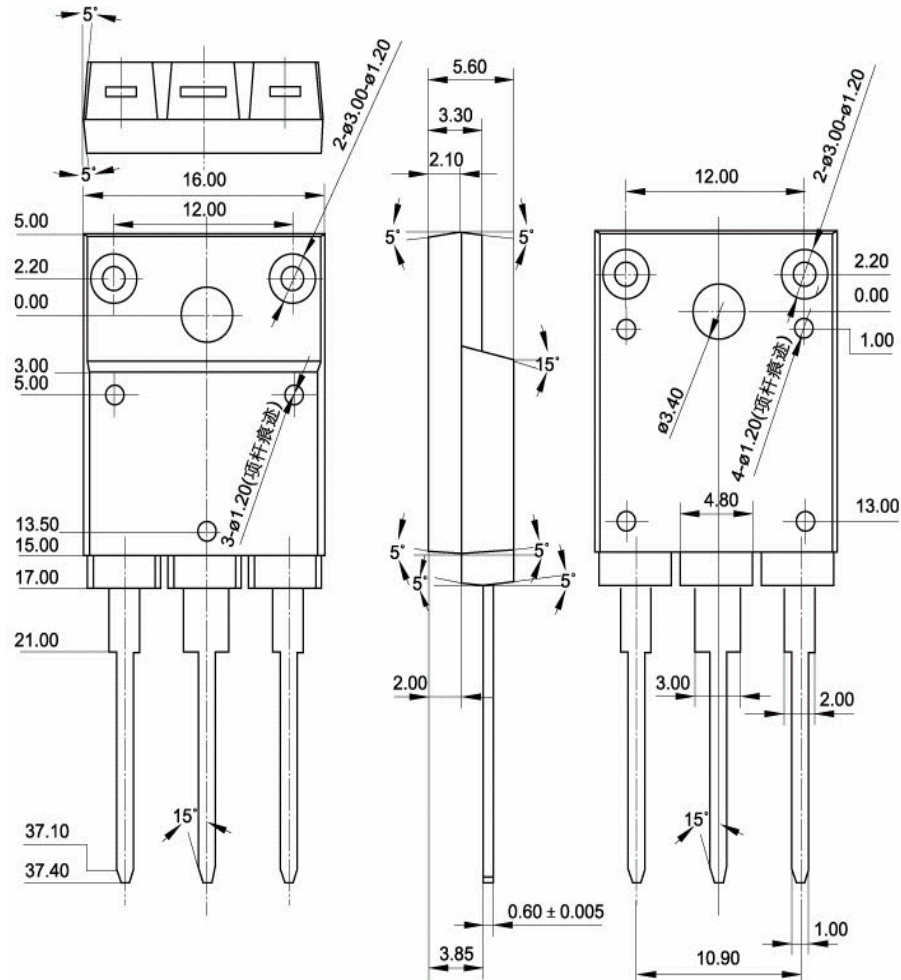


Fig.2 Outline dimensions